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(71) Applicant *(for all designated States except US)*: **MICRON TECHNOLOGY, INC.** [US/US]; 8000 S. Federal Way, Boise, ID 83707-0006 (US).

(72) Inventors; and

(75) Inventors/Applicants *(for US only)*: **CAMPBELL, Kristy, A.** [US/US]; P.O. Box 191171, Boise, ID 83719 (US). **LI, Jiutao** [CN/US]; 5325 E. Branchwood Drive, Boise, ID 83716 (US). **MCTEER, Allen** [US/US]; 208 N. Sierra View Way, Eagle, ID 83616 (US). **MOORE, John, T.** [US/US]; 12530 West Lexus Court, Boise, ID 83713 (US).

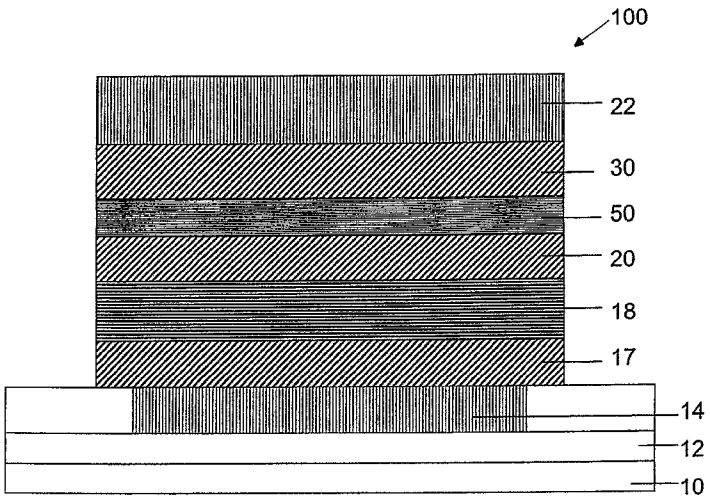
(74) Agent: **D'AMICO, Thomas, J.**; Dickstein Shapiro Morin & Oshinsky LLP, 2101 L Street NW, Washington, DC 20037-1526 (US).

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(54) Title: LAYERED RESISTANCE VARIABLE MEMORY DEVICE AND METHOD OF FABRICATION



(57) Abstract: The invention is related to methods and apparatus for providing a resistance variable memory element with improved data retention and switching characteristics. According to the invention, a resistance variable memory element is provided having at least one metal containing layer (18), preferably a silver-selenide layer, in between two chalcogenide glass layers (17, 20), preferably having Ge_xSe_{100-x} composition, and top and bottom electrodes (14, 22). A metal layer (50), preferably a silver layer, is provided above at least the second chalcogenide glass layer (20) and a conductive adhesion layer (30) is disposed above said silver layer. According to another embodiment of the invention, a resistance variable memory element is provided having a first chalcogenide glass layer (17), a silver layer (40') over said first chalcogenide glass layer, a silver selenide layer (18) over said silver layer, a second chalcogenide glass layer (20) over said silver selenide layer, and optionally a second silver layer over said second chalcogenide glass layer.

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